

AUIRFR5305-VB Datasheet P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
- 60	0.020 at V _{GS} = - 10 V	- 50			
	0.025 at V _{GS} = - 4.5 V	- 45			

FEATURES

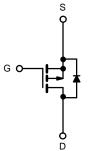
- Trench Power MOSFET
- · Material categorization:



APPLICATIONS

Load Switch





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	- 60	V			
Gate-Source Voltage	V _{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \			
Continuous Drain Current (T _{.1} = 175 °C)	T _C = 25 °C	I_	- 50	Δ.		
Continuous Diam Current (1) = 173 C)	T _C = 125 °C	- I _D	- 40			
Pulsed Drain Current	I _{DM}	- 160	Α			
Avalanche Current	I _{AS}	- 50				
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ		
Dower Dissination	T _C = 25 °C	. P _D	113 ^c	W		
Power Dissipation	T _A = 25 °C	- FD	2.5 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^b	t ≤ 10 s	R _{thJA}	15	18	°C/W	
Junction-to-Ambient ²	Steady State		40	50		
Junction-to-Case		R_{thJC}	0.82	1.1		

Notes:

- a. Duty cycle ≤ 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



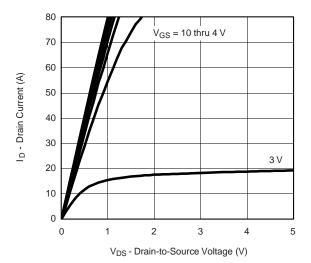
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.5		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50 μA		
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 100	- 100	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			Α	
		V _{GS} = - 10 V, I _D = - 17 A		0.020			
	D	V _{GS} = - 10 V, I _D = - 40 A, T _J = 125 °C		0.030		0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 40 A, T _J = 150 °C		0.035	0.035		
		V _{GS} = - 4.5 V, I _D = - 14 A		0.025			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S	
Dynamic ^b	•				*		
Input Capacitance	C _{iss}			2950			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		380		pF	
Reverse Transfer Capacitance	C _{rss}]		305			
Total Gate Charge ^c	Q_g			110	165		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$		19		nC	
Gate-Drain Charge ^c	Q_{gd}]		28			
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 0.6 Ω		70	105		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -40 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6$		175	260	ns	
Fall Time ^c	t _f	Ω		175	260		
Source-Drain Diode Ratings and Cha	racteristics	Γ _C = 25 °C ^b					
Continuous Current	Is				- 40	^	
Pulsed Current	I _{SM}				- 80	Α	
Forward Voltage ^a	V _{SD}	I _F = - 40 A, V _{GS} = 0 V		- 1	- 1.6	V	
Reverse Recovery Time	t _{rr}	I _F = - 40 A, dI/dt = 100 A/μs		45	70	ns	

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

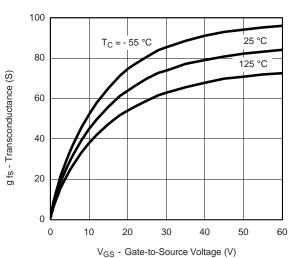
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



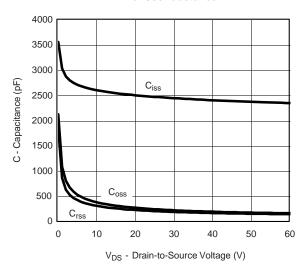
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



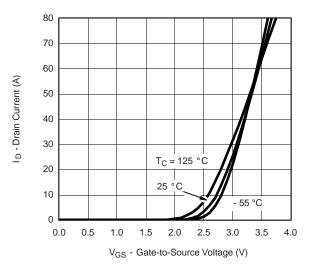
Output Characteristics



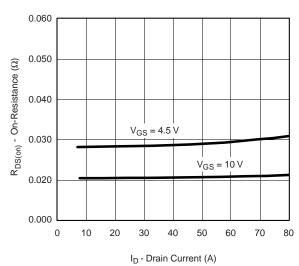
Transconductance



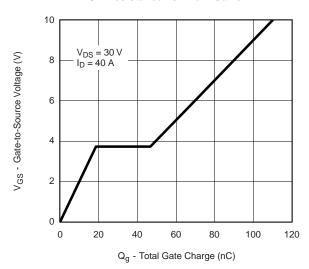
Capacitance



Transfer Characteristics



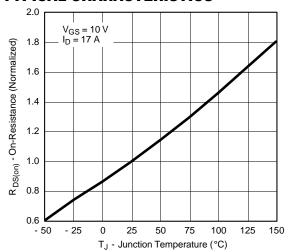
On-Resistance vs. Drain Current



Gate Charge

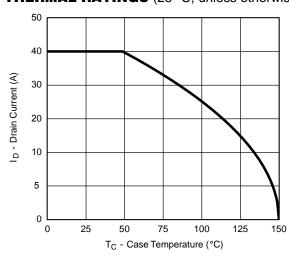


TYPICAL CHARACTERISTICS

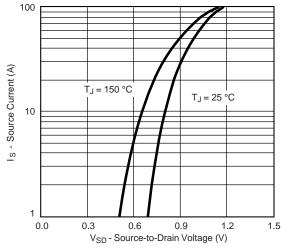


On-Resistance vs. Junction Temperature

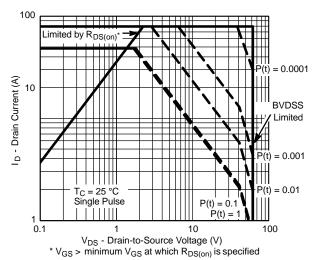
THERMAL RATINGS (25 °C, unless otherwise noted)



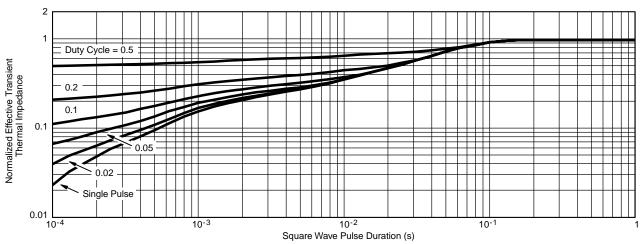
Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



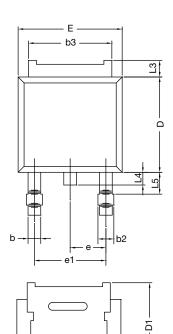
Safe Operating Area



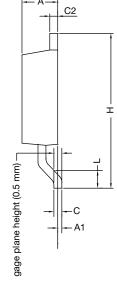
Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE



E1



	MILLIN	METERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28 BSC		0.090 BSC			
e1	4.56	BSC 0.180 BSC		4.56 BSC		BSC
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
FCN: X12-0247-Rev. M. 24-Dec-12						

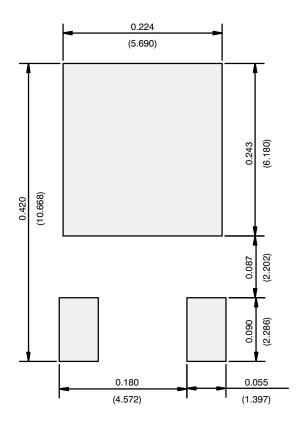
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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